

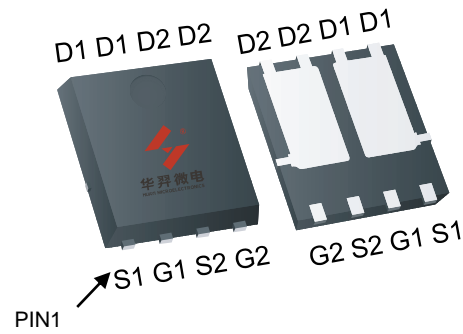


Dual N-Channel Enhancement Mode MOSFET

Feature

- 40V/58A
 $R_{DS(ON)} = 6.9\text{ m}\Omega(\text{typ.}) @ V_{GS} = 10\text{V}$
 $R_{DS(ON)} = 9.6\text{ m}\Omega(\text{typ.}) @ V_{GS} = 4.5\text{V}$
- 100% Avalanche Tested
- Reliable and Rugged
- Halogen Free and Green Devices Available (RoHS Compliant)

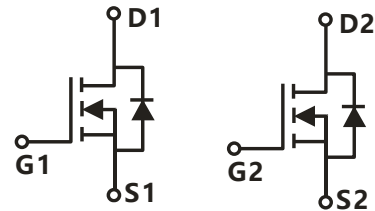
Pin Description



PDFN8L(5x6)

Applications

- Switching Application
- Power Management for DC/DC
- Motor control
- Li-battery protection



Dual N-Channel MOSFET

Ordering and Marking Information

<p>C2 HYG090ND04 XXXYWXXXXX</p>	<p>Package Code C2: PDFN8L(5x6)</p> <p>Date Code XXXYWXXXXX</p>
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Note: HUYI lead-free products contain molding compounds/die attach materials and 100% matte tin plate termination finish, which are fully compliant with RoHS. HUYI lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J-STD-020 for MSL classification at lead-free peak reflow temperature. HUYI defines "Green" to mean lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500ppm by weight).

HUYI reserves the right to make changes, corrections, enhancements, modifications, and improvements to this product and/or to this document at any time without notice.



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit	
Common Ratings (Tc=25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage	40	V	
V _{GSS}	Gate-Source Voltage	±20	V	
T _J	Junction Temperature Range	-55 to 175	°C	
T _{STG}	Storage Temperature Range	-55 to 175	°C	
I _S	Source Current-Continuous(Body Diode)	Tc=25°C	58	A
Mounted on Large Heat Sink				
I _{DM}	Pulsed Drain Current *	Tc=25°C	150	A
I _D	Continuous Drain Current	Tc=25°C	58	A
		Tc=100°C	38	A
P _D	Maximum Power Dissipation	Tc=25°C	55	W
		Tc=100°C	25	W
R _{Jc}	Thermal Resistance, Junction-to-Case		2.74	°C/W
R _{JA}	Thermal Resistance, Junction-to-Ambient		80	°C/W
E _{AS}	SinglePulsed-Avalanche Energy **	L=0.3mH	60	mJ

Note: * Repetitive rating; pulse width limited by max.junction temperature.

** Limited by T_{Jmax} , starting T_J=25°C, L = 0.3mH, R_G= 25 , V_{GS}=10V.

Electrical Characteristics(Tc =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG090ND04LS1			Unit
			Min	Typ.	Max	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40	-		V
I _{DSS}	Drain-to-Source LeakageCurrent	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
		T _J =125°C	-	-	50	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D				

HYG090ND04LS1C2



Electrical Characteristics (Cont.) (T_c =25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	HYG090ND04LS1	Unit
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Typical Operating Characteristics

Figure 1: Power Dissipation

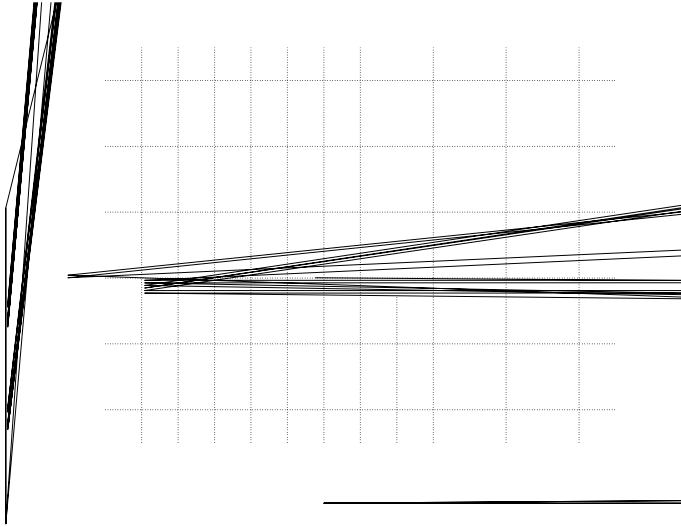


Figure 2: Drain Current

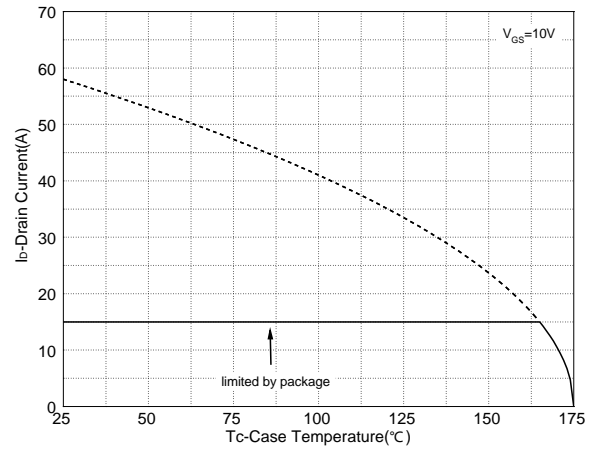


Figure 3: Safe Operation Area

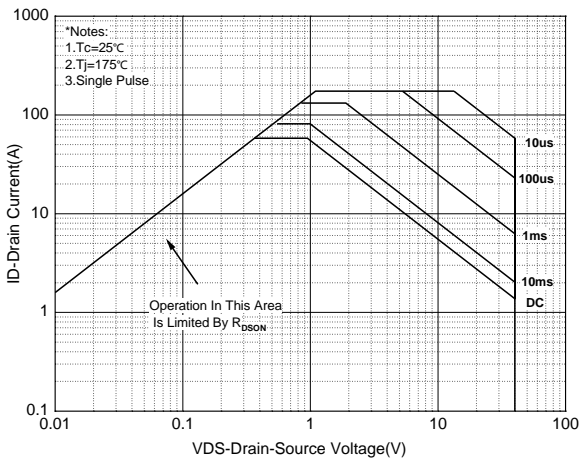


Figure 4: Thermal Transient Impedance

Figure 5: Output Characteristics

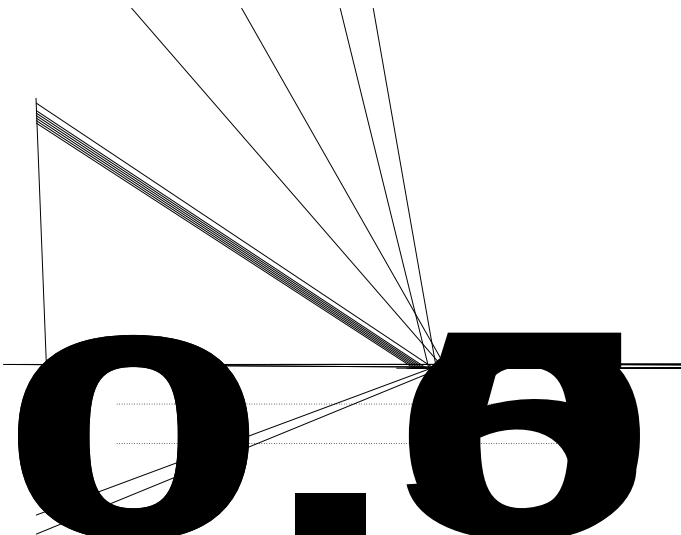
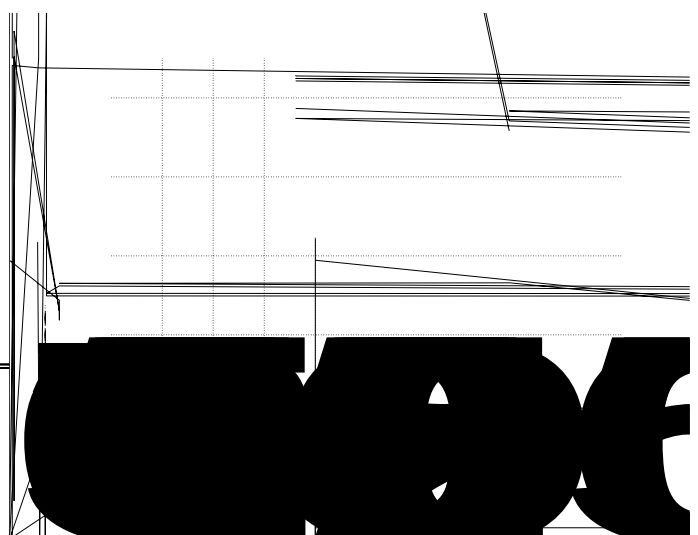


Figure 6: Drain-Source On Resistance





Typical Operating Characteristics(Cont.)

Figure 7: On-Resistance vs. Temperature

Figure 8: Source-Drain Diode Forward

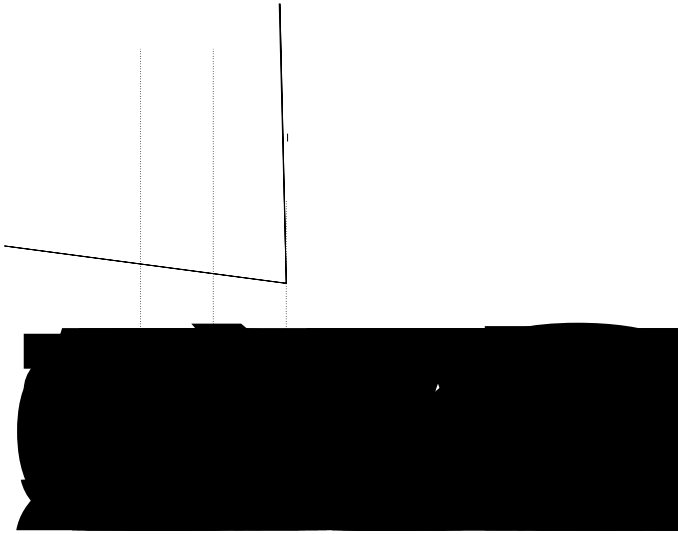
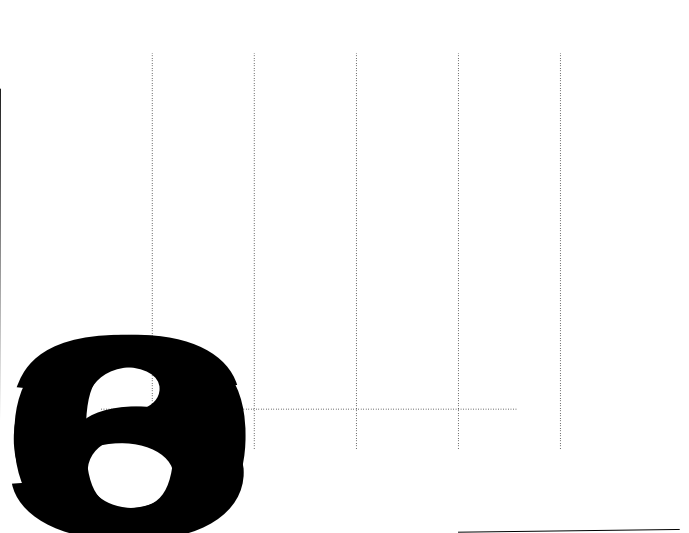
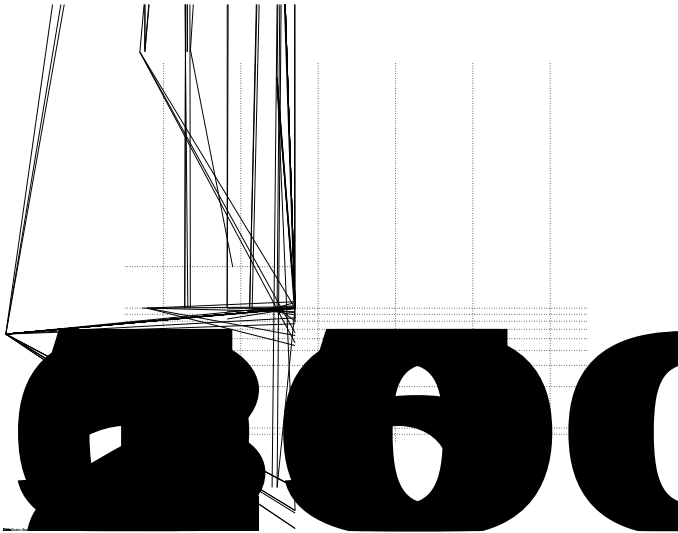


Figure 9: Capacitance Characteristics

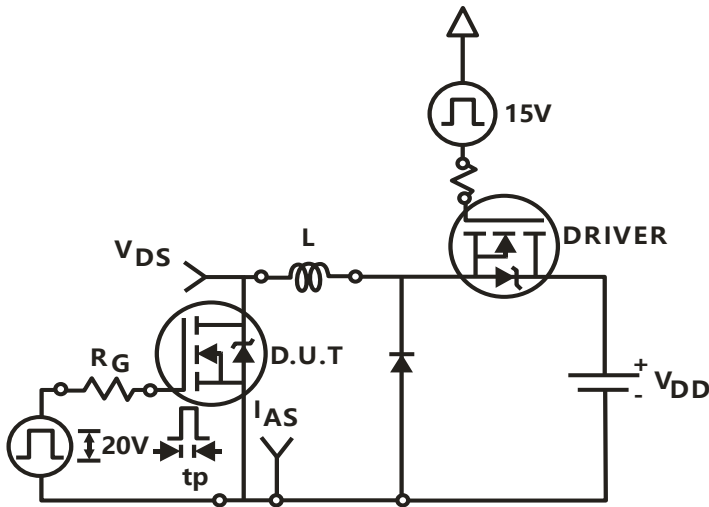
Figure 10: Gate Charge Characteristics



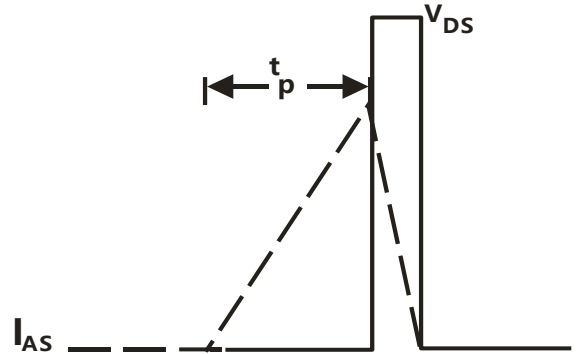


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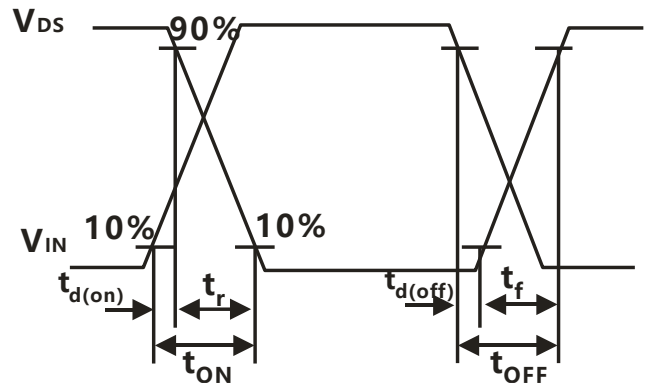
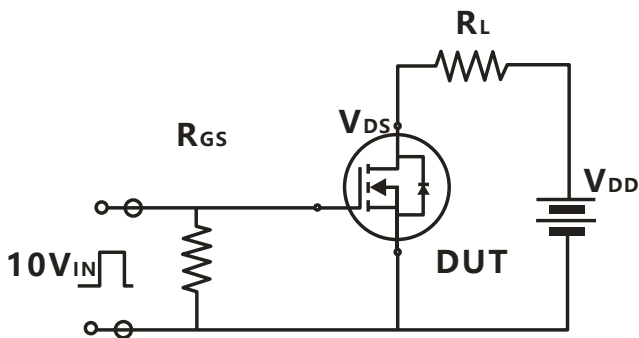
Avalanche Test Circuit



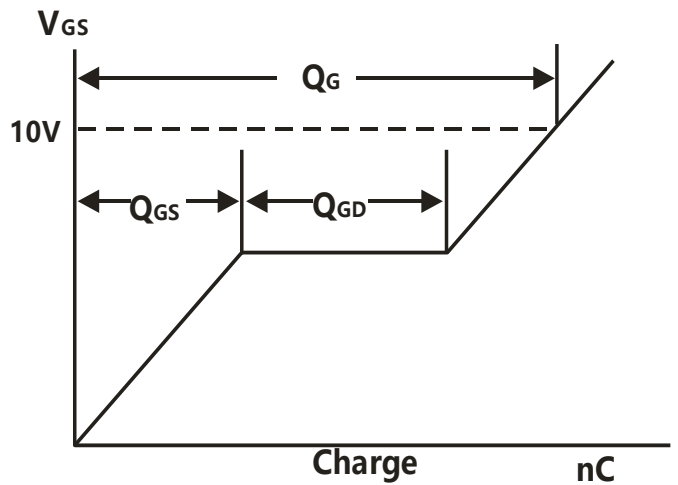
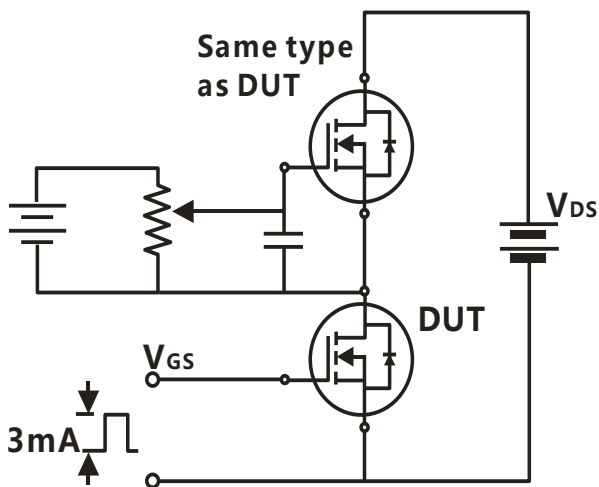
$$E_{AS} = \frac{1}{2} L I_{AS}^2$$



Switching Time Test Circuit



Gate Charge Test Circuit



HYG090ND04LS1C2



Device Per Unit

Package Type	Unit	Quantity
PDFN8L(5x6)	Reel	5000

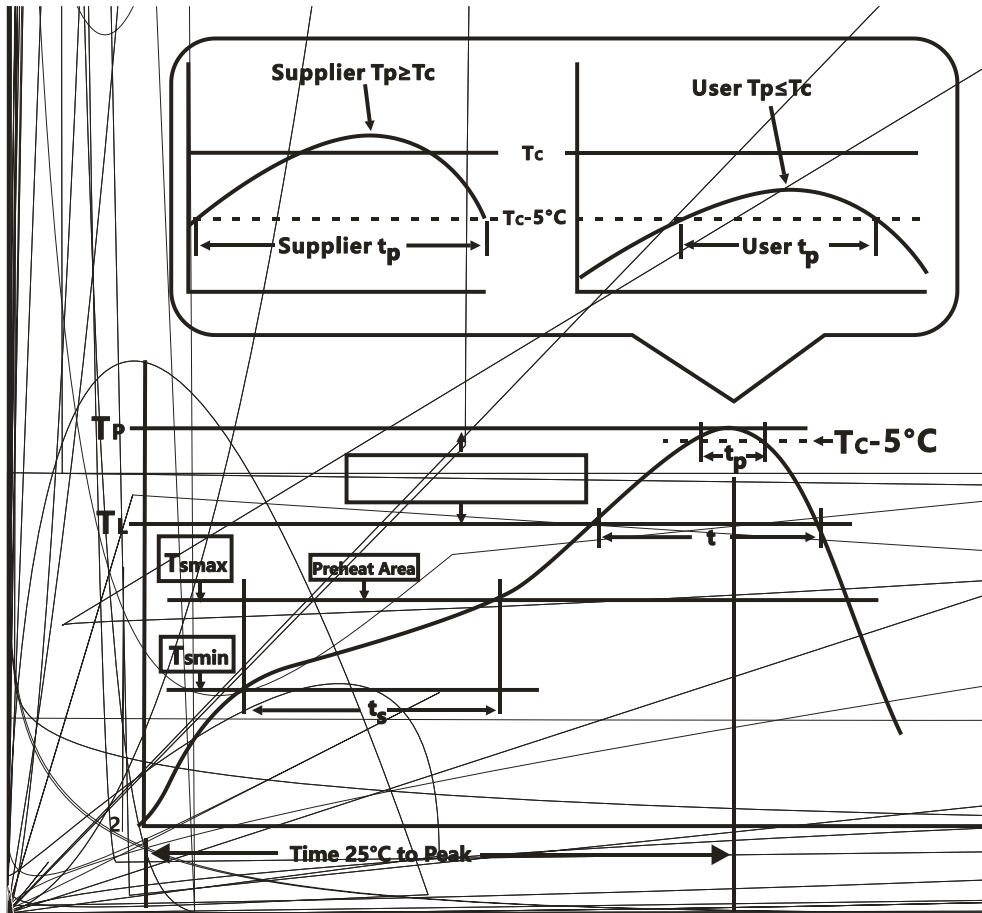
Package Information

PDFN8L(5x6)

COMMON DIMENSIONS			
SYMBOL	mm		
	MIN	NOM	MAX
A	1.00	1.10	1.20
b	0.30	0.40	0.50
c	0.154	0.254	0.354
D1	5.00	5.20	5.40
D2	1.40	1.60	1.80
D3	1.40	1.60	1.80
D4	0.45		



Classification Profile



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Preheat & Soak		
Temperature min (T_{smin})	100 °C	150 °C
Temperature max (T_{smax})	150 °C	200 °C
Time (T_{smin} to T_{smax}) (t_s)	60-120 seconds	60-120 seconds
Average ramp-up rate (T_{smax} to T_p)	3 °C/second max.	3°C/second max.
Liquidous temperature (T_L)	183 °C	217 °C
Time at liquidous (t_L)	60-150 seconds	60-150 seconds
Peak package body Temperature (T_p)*	See Classification Temp in table 1	See Classification Temp in table 2
Time (t_p)** within 5°C of the specified classification temperature (T_c)	20** seconds	30** seconds
Average ramp-down rate (T_p to T_{smax})	6 °C/second max.	6 °C/second max.
Time 25°C to peak temperature	6 minutes max.	8 minutes max.
*Tolerance for peak profile Temperature (T_p) is defined as a supplier minimum and a user maximum.		
** Tolerance for time at peak profile temperature (t_p) is defined as a supplier minimum and a user maximum.		



Table 1. SnPb Eutectic Process – Classification Temperatures (Tc)

Package Thickness	Volume mm³ <350	Volume mm³ ≥350
<2.5 mm	235 °C	220 °C
≥2.5 mm	220 °C	220 °C

Table 2. Pb-free Process – Classification Temperatures (Tc)

Package Thickness	Volume mm³ <350	Volume mm³ 350-2000	Volume mm³ ≥2000
<1.6 mm	260 °C	260 °C	260 °C
1.6 mm – 2.5 mm	260 °C	250 °C	245 °C
≥2.5 mm			